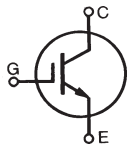
IXYS

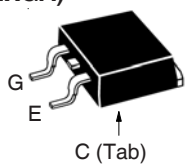
HiPerFAST™ IGBTs
B2-Class High Speed

IXGA16N60B2
IXGP16N60B2

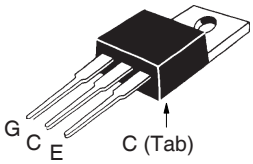
V_{CES} = 600V
I_{C110} = 16A
$V_{CE(sat)}$ ≤ 2.3V
$t_{fi(typ)}$ = 70ns



TO-263 AA (IXGA)



TO-220AB (IXGP)



G = Gate C = Collector
E = Emitter Tab = Collector

Symbol	Test Conditions	Maximum Ratings	
V_{CES}	T_J = 25°C to 150°C	600	V
V_{CGR}	T_J = 25°C to 150°C, R_{GE} = 1MΩ	600	V
V_{GES}	Continuous	±20	V
V_{GEM}	Transient	±30	V
I_{C25}	T_C = 25°C	40	A
I_{C110}	T_C = 110°C	16	A
I_{CM}	T_C = 25°C, 1ms	100	A
SSOA (RBSOA)	V_{GE}= 15V, T_J = 125°C, R_G = 22Ω Clamped Inductive load	I_{CM} = 32 $V_{CE} \le V_{CES}$	A
P_C	T_C = 25°C	150	W
T_J		-55 ... +150	°C
T_{JM}		150	°C
T_{stg}		-55 ... +150	°C
M_d	Mounting Torque (TO-220)	1.13/10	Nm/lb.in.
F_C	Mounting Force (TO-263)	10..65 / 2.2..14.6	N/lb.
T_L	Maximum Lead Temperature for Soldering	300	°C
T_{SOLD}	1.6mm (0.062 in.) from Case for 10s	260	°C
Weight	TO-263	2.5	g
	TO-220	3.0	g

Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
$V_{GE(th)}$	I_C = 250μA, V_{CE} = V_{GE}	3.0		5.5	V
I_{CES}	V_{CE} = V_{CES}, V_{GE} = 0V			15	μA
	T_J = 125°C			250	μA
I_{GES}	V_{CE} = 0V, V_{GE} = ±20V			±100	nA
$V_{CE(sat)}$	I_C = 12A, V_{GE} = 15V, Note1			2.30	V
	T_J = 125°C		1.65		V

Features

- Optimized for Low Conduction and Switching Losses
- Square RBSOA
- International Standard Packages

Advantages

- High Power Density
- Low Gate Drive Requirement

Applications

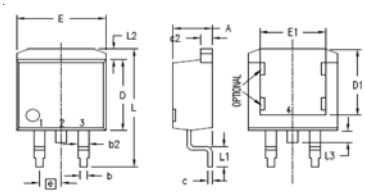
- Power Inverters
- UPS
- Motor Drives
- SMPS
- PFC Circuits
- Battery Chargers
- Welding Machines
- Lamp Ballasts

Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
g_{fs}	I_C = 12A, V_{CE} = 10V, Note 1	8			S
C_{ies}	V_{CE} = 25V, V_{GE} = 0V, f = 1MHz		675		pF
C_{oes}			60		pF
C_{res}			20		pF
$Q_{g(on)}$	I_C = 12A, V_{GE} = 15V, V_{CE} = 0.5 • V_{CES}		24		nC
Q_{ge}			5		nC
Q_{gc}			13		nC
$t_{d(on)}$	**Inductive load, T_J = 25°C**		18		ns
t_{ri}	I_C = 12A, V_{GE} = 15V		20		ns
E_{on}	V_{CE} = 400V, R_G = 22Ω		0.16		mJ
$t_{d(off)}$	Note 2		73		ns
t_{fi}			70		ns
E_{off}			0.12	0.22	mJ
$t_{d(on)}$	**Inductive load, T_J = 125°C**		17		ns
t_{ri}	I_C = 12A, V_{GE} = 15V		20		ns
E_{on}	V_{CE} = 400V, R_G = 22Ω		0.26		mJ
$t_{d(off)}$	Note 2		140		ns
t_{fi}			125		ns
E_{off}			0.38		mJ
R_{thJC}				0.83	°C/W
R_{thCK}	TO-220		0.50		°C/W

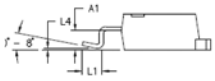
Notes:

1. Pulse test, t ≤ 300µs, duty cycle, d ≤ 2%.
2. Switching times & energy losses may increase for higher V_{CE}(Clamp), T_J or R_G.

TO-263 (IXGA) Outline

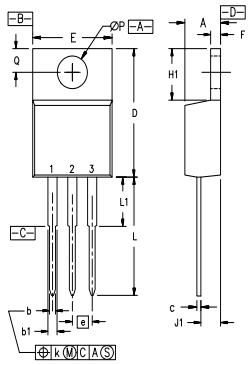


1 = Gate
2 = Collector
3 = Emitter
4 = Collector



SYM	INCHES MIN	INCHES MAX	MILLIMETERS MIN	MILLIMETERS MAX
A	.160	.190	4.06	4.83
A1	.080	.110	2.03	2.79
b	.020	.039	0.51	0.99
b2	.045	.055	1.14	1.40
c	.016	.029	0.40	0.74
c2	.045	.055	1.14	1.40
D	.340	.380	8.64	9.65
D1	.315	.350	8.00	8.89
E	.380	.410	9.65	10.41
E1	.245	.320	6.22	8.13
e	.100 BSC		2.54 BSC	
L	.575	.625	14.61	15.88
L1	.090	.110	2.29	2.79
L2	.040	.055	1.02	1.40
L3	.050	.070	1.27	1.78
L4	0	.005	0	0.13

TO-220 (IXGP) Outline



1 = Gate 2 = Collector
3 = Emitter

SYM	INCHES MIN	INCHES MAX	MILLIMETERS MIN	MILLIMETERS MAX
A	.170	.190	4.32	4.83
b	.025	.040	0.64	1.02
b1	.045	.065	1.15	1.65
c	.014	.022	0.35	0.56
D	.580	.630	14.73	16.00
E	.390	.420	9.91	10.66
e	.100 BSC		2.54 BSC	
F	.045	.055	1.14	1.40
H1	.230	.270	5.85	6.85
J1	.090	.110	2.29	2.79
k	0	.015	0	0.38
L	.500	.550	12.70	13.97
L1	.110	.230	2.79	5.84
ØP	.139	.161	3.53	4.08
Q	.100	.125	2.54	3.18

Fig. 1. Output Characteristics @ T_J = 25ºC

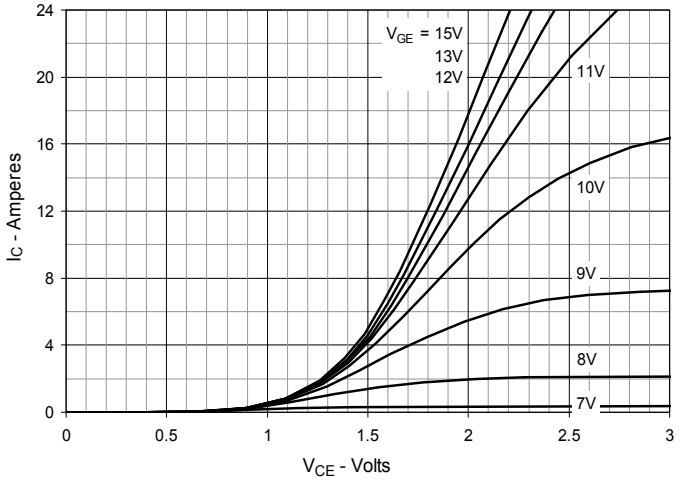


Fig. 2. Extended Output Characteristics @ T_J = 25ºC

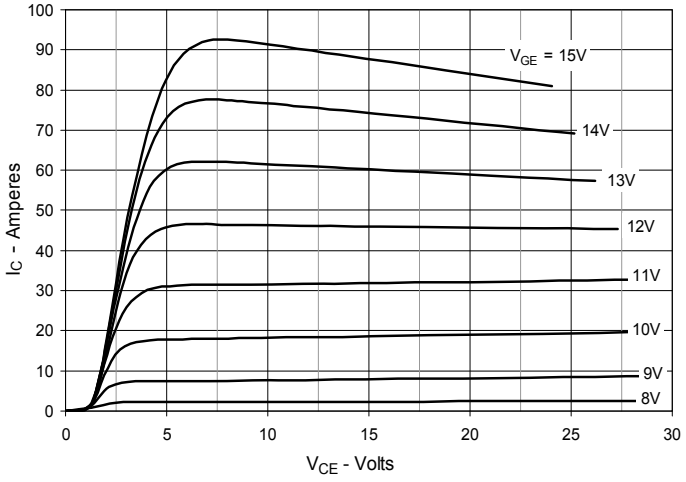


Fig. 3. Output Characteristics @ T_J = 125ºC

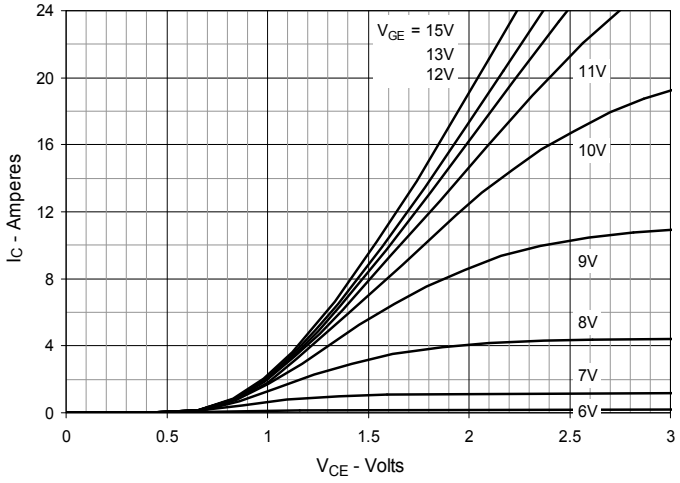


Fig. 4. Dependence of $V_{CE(sat)}$ on Junction Temperature

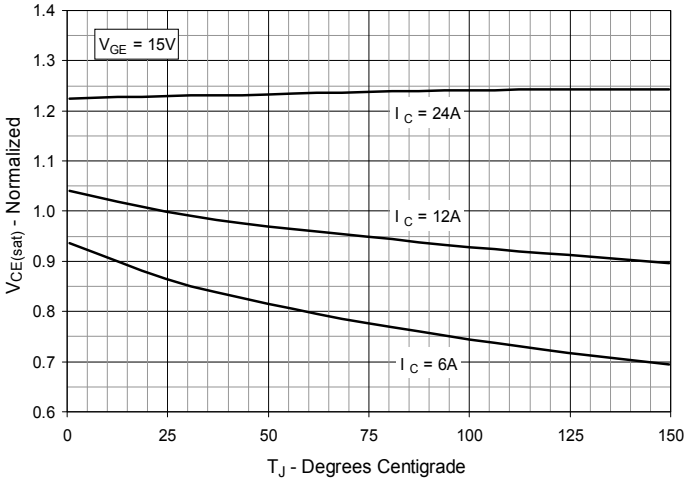


Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

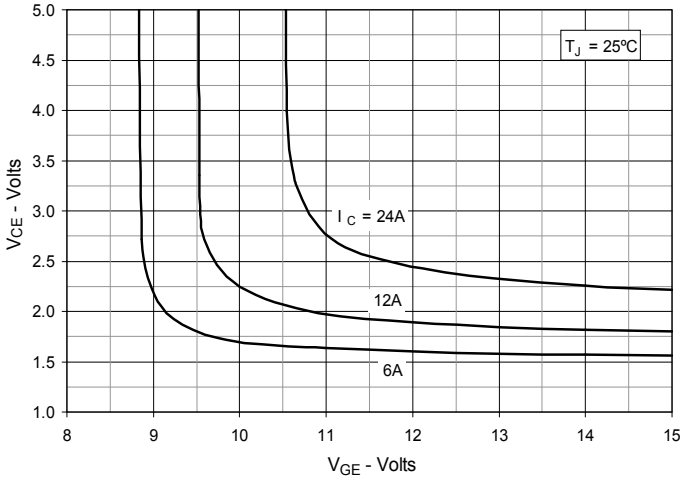


Fig. 6. Input Admittance

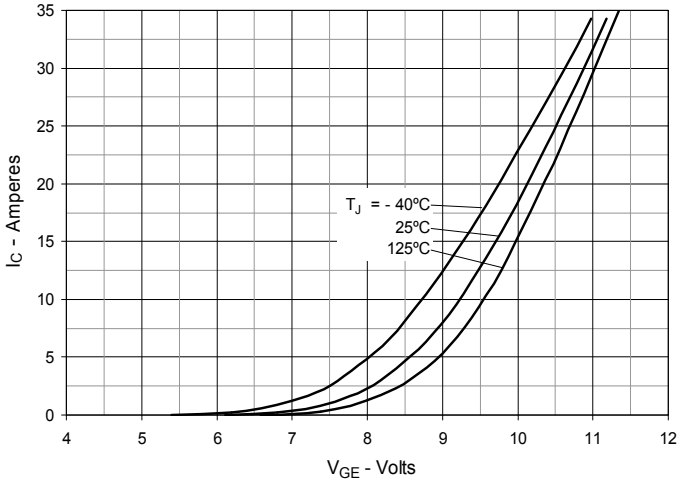


Fig. 7. Transconductance

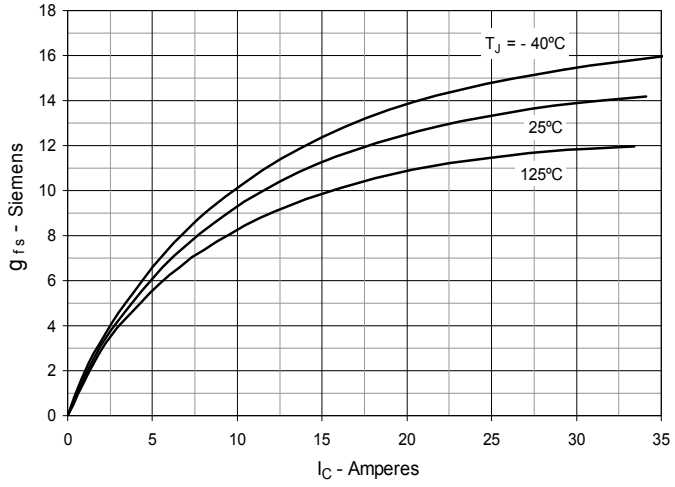


Fig. 8. Gate Charge

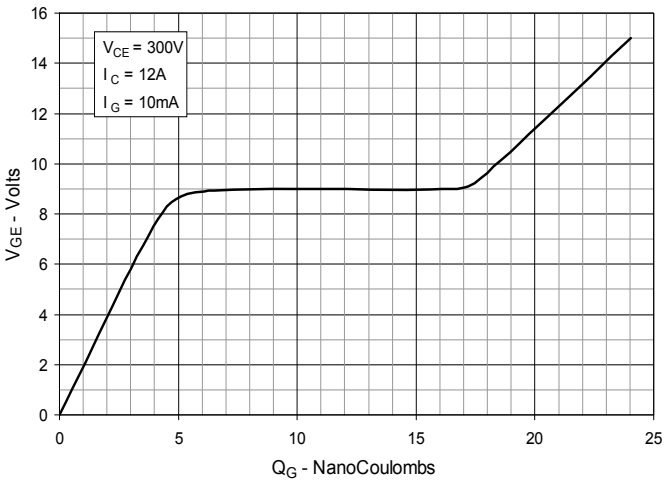


Fig. 9. Capacitance

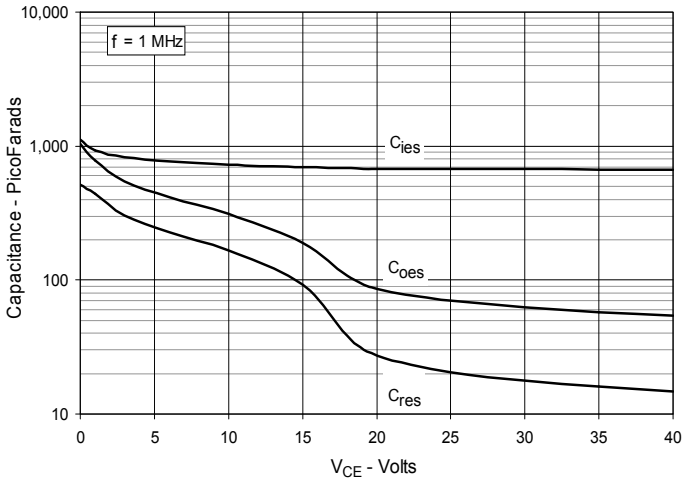


Fig. 10. Reverse-Bias Safe Operating Area

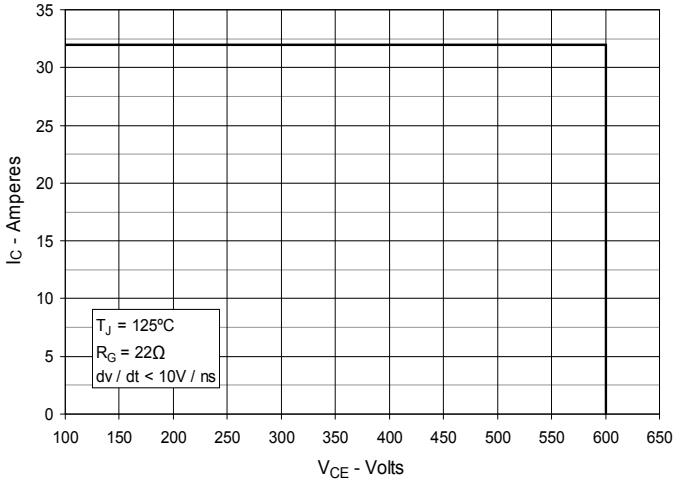


Fig. 11. Maximum Transient Thermal Impedance

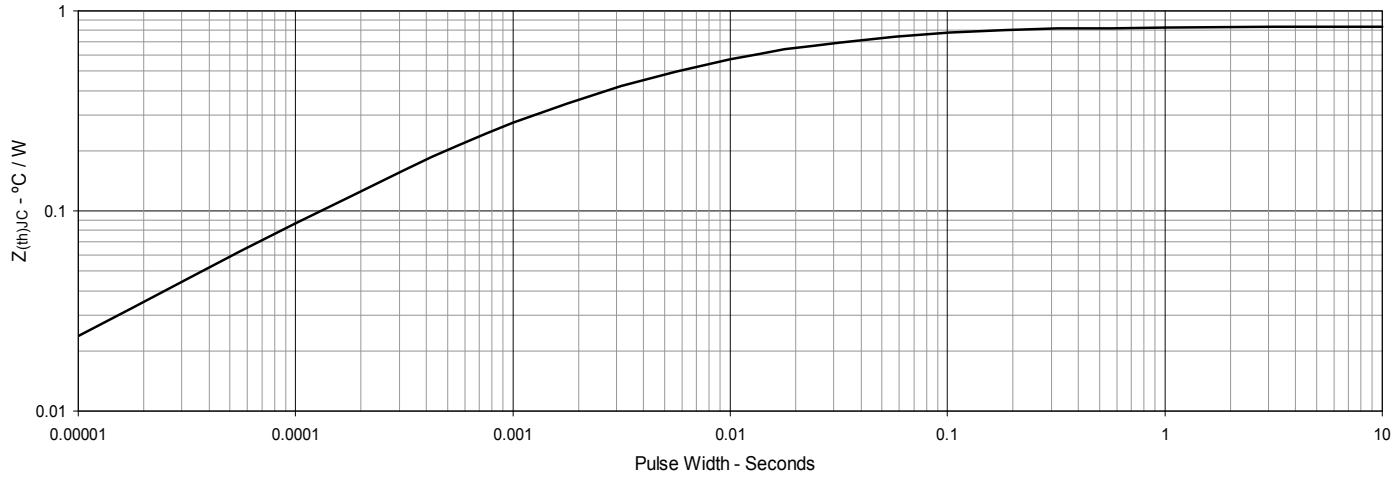


Fig. 12. Inductive Switching Energy Loss vs. Gate Resistance

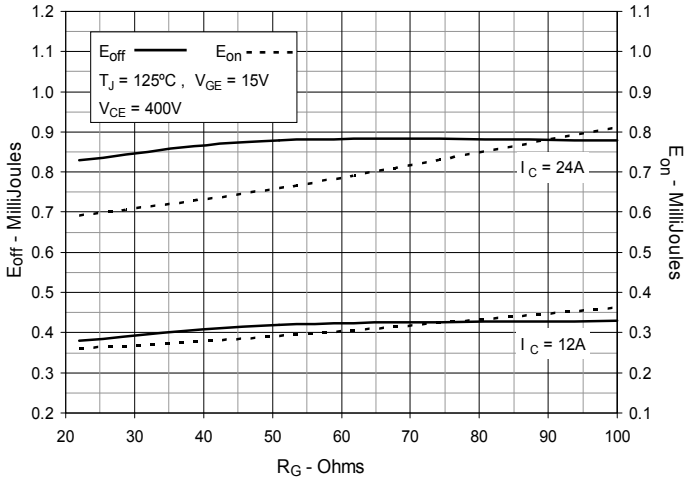


Fig. 13. Inductive Switching Energy Loss vs. Collector Current

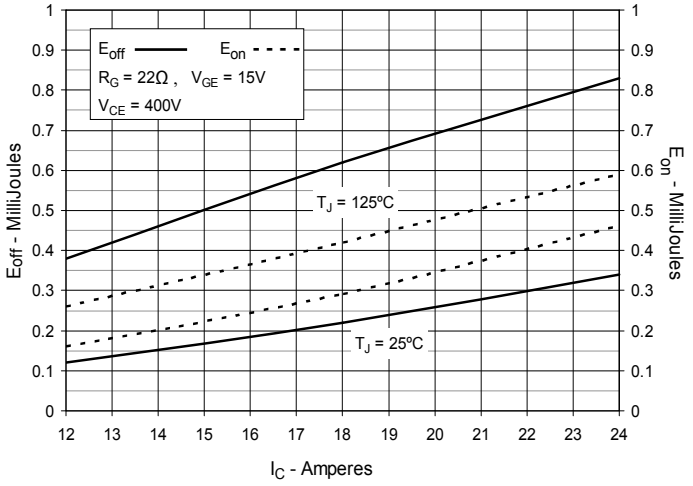


Fig. 14. Inductive Switching Energy Loss vs. Junction Temperature

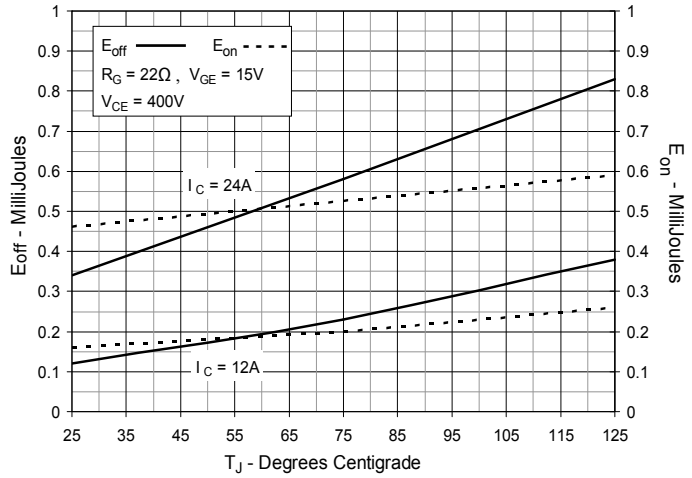


Fig. 15. Inductive Turn-off Switching Times vs. Gate Resistance

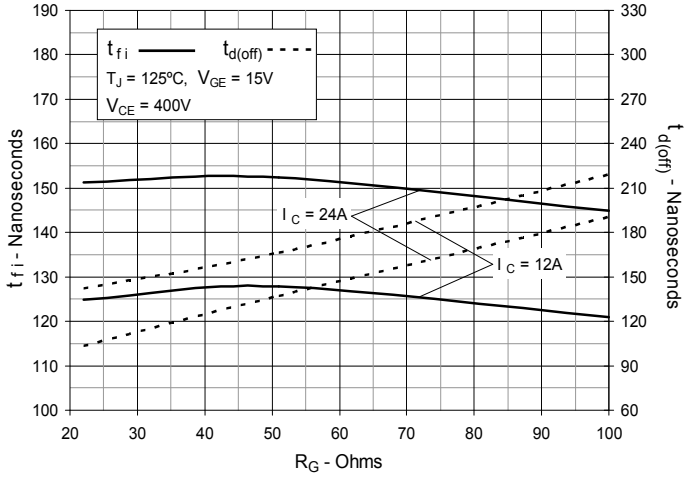


Fig. 16. Inductive Turn-off Switching Times vs. Collector Current

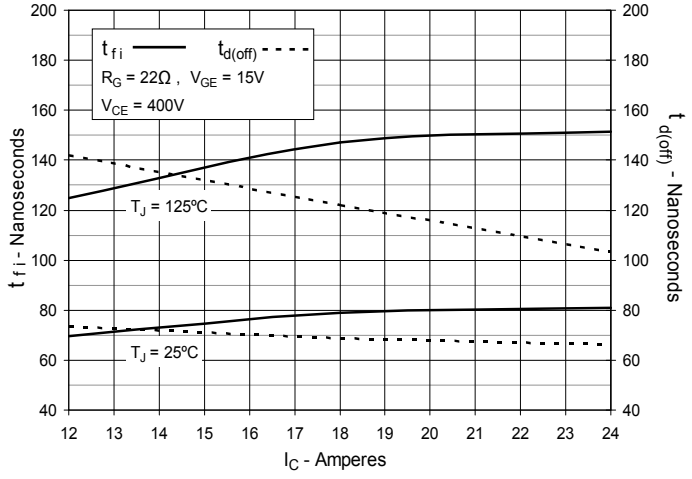


Fig. 17. Inductive Turn-off Switching Times vs. Junction Temperature

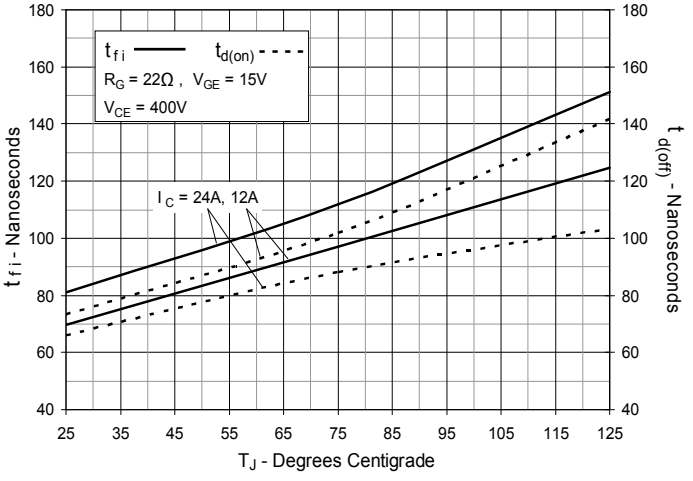


Fig. 18. Inductive Turn-on Switching Times vs. Gate Resistance

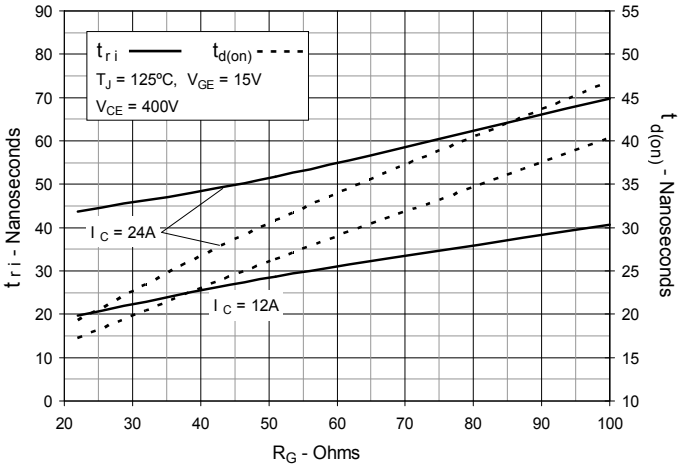


Fig. 19. Inductive Turn-on Switching Times vs. Collector Current

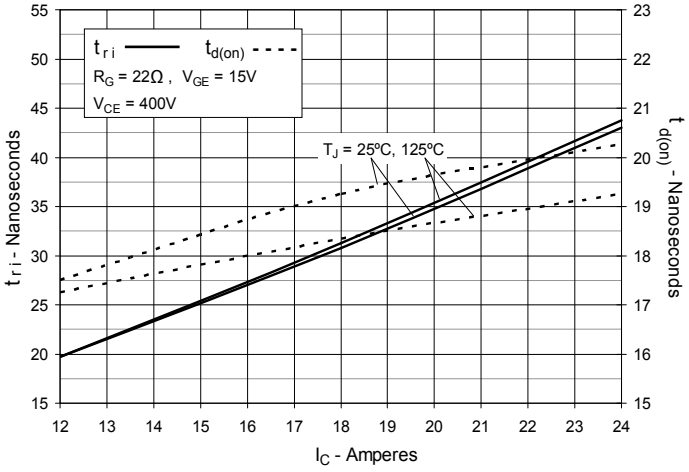


Fig. 20. Inductive Turn-on Switching Times vs. Junction Temperature